Micross Components in partnership with Clifton Semiconductor offers a High Performance range of Gallium Arsenide Products

Efficiency – Performance – Temperature range

With lower power consumption, greater recovery speed, wider operating temperature range, lower weight, smaller dimensions and better radiation hardness, Cliftons GaAs products are intended for use in high-tech power electronics solutions, ranging from automotive and household appliances to military, aviation and space electronics. Users can gain considerable benefits in power system design due to lower weight, smaller size and reduced cooling requirements. Coupled with increased efficiency, durability and reliability, at higher operating frequencies, challenges and overtakes traditional Silicon products.

Can't have it all? With Micross Components range of GaAs PiN diodes, you can …

- High Voltage, VRRM up to 1300V
- High Current, up to 200A
- Low voltage drop, VF < 1.6V at IFMax
- Very low leakage currents < 1.1mA @ TJ = 260°C & VR = VRRM!!!
- High Temperature, TJ of 260°C, compared with Silicon's 175°C
- Ultrafast switching/commutating speeds, ˜ 30nS @ _IF/_t=200A/uS
- Low junction capacitance, typically 18pF
- Radiation tolerant, contact the factory for information

Applications for GaAs Products:

- Automotive
- Military
- Mining
- Power Supply
- Commercial
- Space
- Aviation
- Railway

GaAs features:

- Higher Tj max than current Si, SiC, GaN products.
- Higher power density per surface area.
- Dynamics independent of temperature change.
- Naturally low capacitance

These devices are available from Micross Components as both die product, or as packaged devices in a wide variety of package formats. Contact Micross Components for further details.

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